L Number	Hits	Search Text	DB	Time stamp
1	115	(257/E21.623).CCLS.	USPAT;	2004/03/04 16:39
-		(10), 111, 110, 110, 110, 110, 110, 110,	US-PGPUB;	
İ			EPO; JPO;	
			DERWENT;	!
			IBM TDB	
_	705	"T-shaped gate" or "T-shaped transistor" or	USPAT;	2004/03/04 16:43
2	/05		1	2004/03/04 16:43
		"T-shaped electrode"	US-PGPUB;	1
			EPO; JPO;	
İ			DERWENT;	<u> </u>
İ			IBM_TDB	1
3	629	"T-shaped gate" or "T-shaped transistor" or	USPAT;	2004/03/04 17:49
] [		"T-shaped electrode"	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
4	154	damascene adj gate	USPAT;	2004/03/04 16:49
			EPO; JPO;	
			DERWENT;	!
			IBM TDB	
5	10	("4577392"   "5808340"   "5844836"	USPAT	2004/03/04 17:01
	10	"5960271"   "6008132"   "6044007"	OBIAI	2004/03/04 17:01
}				1
		"6107667"   "6136674"   "6159781"		1
_	_	"6333273").PN.		1 2224 /22 /23 27 27
6	0	6551941.URPN.	USPAT	2004/03/04 17:01
7	1	("4341850").PN.	USPAT	2004/03/04 17:49
8	8	("3849136"   "3867148"   "3873361"	USPAT	2004/03/04 17:50
j		"3971860"   "4024293"   "4109029"		
]		"4165395" "4283483").PN.		1
ا وا	11	4341850.URPN.	USPAT	2004/03/04 17:50
_	100	(fin near fet) or FINFET	USPAT;	2004/03/04 16:27
	100	(IIII hear ree) or rinibr	US-PGPUB;	2001,03,01 1012.
			EPO; JPO;	]
				1
			DERWENT;	
			IBM_TDB	10001/00/01 10 07
-	84	(notch near gate) and semiconductor	USPAT;	2004/03/04 13:27
			US-PGPUB;	
			EPO; JPO;	
İ			DERWENT;	
			IBM_TDB	1
-	191	notch near gate	USPAT;	2004/03/04 13:49
		_	US-PGPUB;	
			EPO; JPO;	•
			DERWENT;	
			IBM TDB	
_	13	notch near transistor	USPAT;	2004/03/04 13:58
-	13	notch near transistor		2004/03/04 13:58
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
]			IBM_TDB	
-	16	notch near FET	USPAT;	2004/03/04 13:58
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	16	("5045488"   "5095344"   "5198380"	USPAT	2004/03/04 13:59
-	10	'	OUTAI	2004/03/04 13:39
1		l ! ! ! !		
		"5268319"   "5270240"   "5342801"		
		"5408136"   "5455792"   "5554553"		
		"5554564"   "5572054"   "5714412"		
]		"5897353").PN.		
-	7		USPAT	2004/03/04 14:27
-	476	((438/259) or (438/260)).CCLS.	USPAT;	2004/03/04 14:40
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	10405	(applied near materials).as.	USPAT;	2004/03/04 14:40
-	10495	(appried hear materials).as.	1	2004/03/04 14:40
			US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
1			IBM TDB	1

-	188	((applied near materials).as.) and notch	USPAT;	2004/03/04 14:42
			US-PGPUB;	
			EPO; JPO;	
		, ·	DERWENT;	
			IBM_TDB	
-	10008	notch and gate	USPAT;	2004/03/04 14:42
			US-PGPUB;	İ
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2350	(notch and gate) and semiconductor	USPAT;	2004/03/04 14:42
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	245	, , ,	USPAT;	2004/03/04 14:53
		amorphous	US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	54	"V-shaped gate"	USPAT;	2004/03/04 14:53
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	